

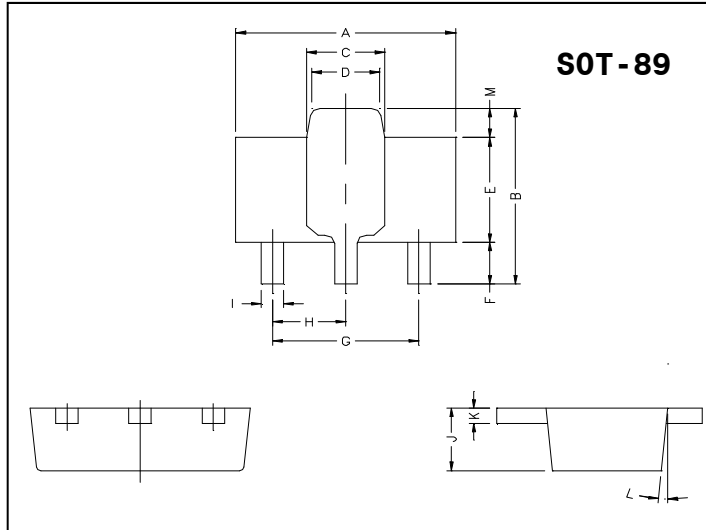
GM5551

NPN EPITAXIAL PLANAR TRANSISTOR

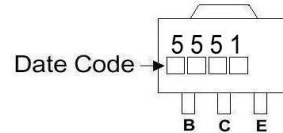
Description

The GM5551 is designed for for general purpose applications requiring high breakdown voltages.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

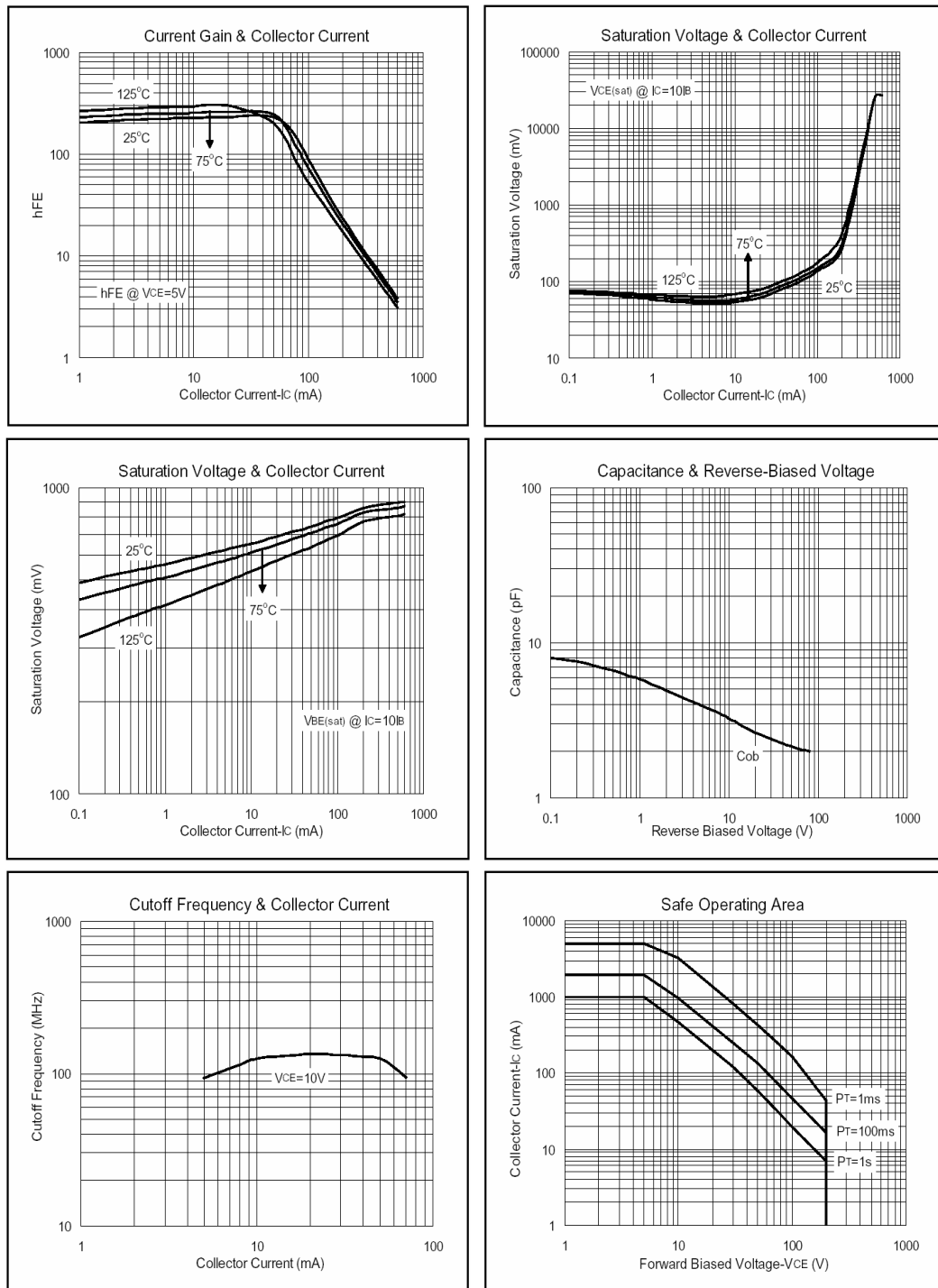
Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	180	V
Collector to Emitter Voltage	VCES	160	V
Emitter to Base Voltage	VEBO	6.0	V
Collector Current	I _C	600	mA
Total Power Dissipation	PD	1.2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	180	-	-	V	I _C =100uA
BVCEO	160	-	-	V	I _C =1mA
BVEBO	6	-	-	V	I _E =10uA
ICBO	-	-	50	nA	VCB=120V
IEBO	-	-	50	nA	VEB=4V
VCE(sat)1	-	-	150	mV	I _C =10mA, I _B =1mA
VCE(sat)2	-	-	200	mV	I _C =50mA, I _B =5mA
VBE(sat)1	-	-	1	V	I _C =10mA, I _B =1mA
VBE(sat)2	-	-	1	V	I _C =50mA, I _B =5mA
hFE1	80	-	-		VCE=5V, I _C =1mA
hFE2	80	-	250		VCE=5V, I _C =10mA
hFE3	30	-	-		VCE=5V, I _E =50mA
f _T	100		300	MHz	VCE=10V, I _C =10mA, f=100MHz
Cob	-	-	6	pF	VCB=10V, f=1MHz

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD., Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 FAX : 86-21-38950165